



### 20V P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on) max</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
-20V	$35m\Omega @ V_{GS} = -4.5V$	-6.0A
-200	$45 \text{m}\Omega @ V_{GS} = -2.5V$	-5.2A

### **Description**

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

### **Applications**

- DC-DC Converters
- Motor Control
- Power management functions
- Analog Switch

### **Features and Benefits**

- Low Input Capacitance
- Low On-Resistance
- · Fast Switching Speed
- ESD protected Up To 3KV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Mechanical Data**

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.013 grams (Approximate)

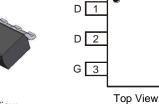
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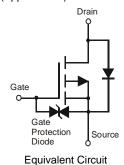
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TSOT26





Top View

### Ordering Information (Note 5)

Part Number	Case	Packaging
DMP2035UVTQ-7	TSOT26	3,000/Tape & Reel
DMP2035UVTQ-13	TSOT26	10,000/Tape & Reel

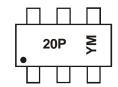
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

Pin-Out

- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q10x qualified and are PPAP capable. Automotive, AEC-Q10x and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_compliance\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



20P = Product Type Marking Code YM = Date Code Marking Y = Year (ex: Y = 2011) M = Month (ex: 9 = September)

Date Code Key

Year	201	1	2012		2013	20	14	2015		2016	2	2017
Code	Υ		Z		Α		3	С		D		Е
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# 

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		$V_{DSS}$	-20	V	
Gate-Source Voltage			V <sub>GSS</sub>	±12	V
		$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	-6.0 -4.8	А
Continuous Drain Current (Note 7) V <sub>GS</sub> = -4.5V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	-7.2 -5.7	А
Continuous Prain Current (Note 7) // 25/	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	-5.2 -4.1	А
Continuous Drain Current (Note 7) V <sub>GS</sub> = -2.5V	t<10s	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	-6.2 -4.9	А
Maximum Continuous Body Diode Forward Current	t (Note 7)	I <sub>S</sub>	-2.0	А	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	-24	А		

### **Thermal Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)		$P_{D}$	1.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	106	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s		74	
Total Power Dissipation (Note 7)		$P_{D}$	2.0	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	r.	65	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	t<10s	$R_{\theta JA}$	46	
Thermal Resistance, Junction to Case (Note 7)	Steady State	$R_{ heta JC}$	11.8	
Operating and Storage Temperature Range		$T_{J_{I}}T_{STG}$	-55 to 150	°C

### Electrical Characteristics @TA = 25°C unless otherwise specified

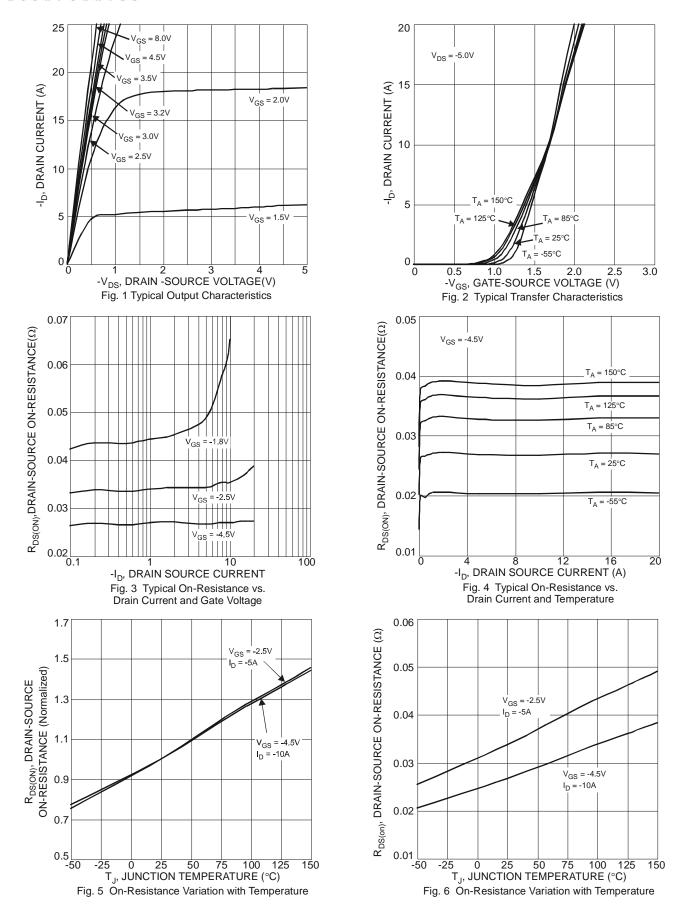
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1	μΑ	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(th)}$	-0.4	-0.7	-1.5	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Gate Threshold Voltage Temperature Coefficient	$_{\triangle}V_{GS(th)}/_{\triangle}T_{J}$	_	2.5	_	mV/°C	$I_D = -250\mu A$ , Referenced to +25°C	
		_	23	35		$V_{GS} = -4.5V, I_D = -4.0A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	30	45	mΩ	$V_{GS} = -2.5V, I_{D} = -4.0A$	
		_	41	62		$V_{GS} = -1.8V, I_D = -2.0A$	
Forward Transfer Admittance	Y <sub>fs</sub>	_	18		S	$V_{DS} = -5V, I_{D} = -5.5A$	
Diode Forward Voltage (Note 7)	V <sub>SD</sub>	_	-0.7	-1.0	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C <sub>iss</sub>	_	1610	2400		101/11/	
Output Capacitance	Coss	_	157	210	pF	$V_{DS} = -10V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	145	200		1 = 1.0WH2	
Gate Resistance	$R_{G}$	_	9.4	14.1	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge	$Q_{g}$	_	15.4	23.1		V 40V V 45V	
Gate-Source Charge	$Q_{gs}$	_	2.5	_	nC	$V_{DS} = -10V, V_{GS} = -4.5V$ $I_{D} = -4A$	
Gate-Drain Charge	$Q_{gd}$	_	3.3	_		ID = -4A	
Turn-On Delay Time	t <sub>D(on)</sub>	_	17	33			
Turn-On Rise Time	t <sub>r</sub>	_	12	19		$V_{GS} = -4.5V$ , $V_{DS} = -10V$ , $R_G = 6\Omega$ ,	
Turn-Off Delay Time	t <sub>D(off)</sub>	_	94	150	ns	$I_D = -1A$ , $R_L = 10\Omega$	
Turn-Off Fall Time	t <sub>f</sub>	_	42	64			
Reverse Recovery Time	t <sub>rr</sub>		14	25	ns	1 4 5 \ di/dt 400 \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Reverse Recovery Charge	Q <sub>rr</sub>	_	4	8	nC	I <sub>F</sub> =-4.5A, di/dt=100A/μS	

6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

<sup>7.</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

<sup>8.</sup> Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.







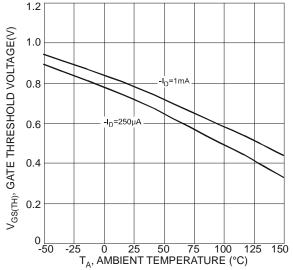


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

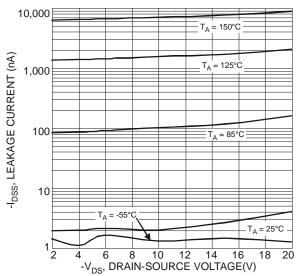
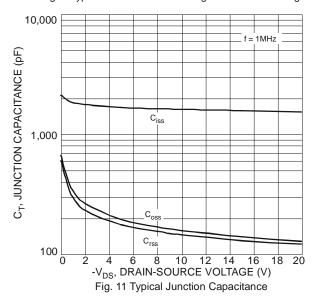
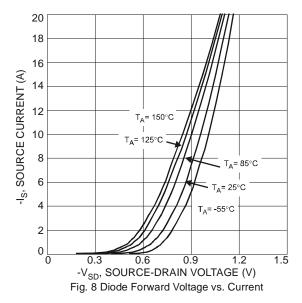


Fig. 9 Typical Drain-Source Leakage Current vs. Voltage





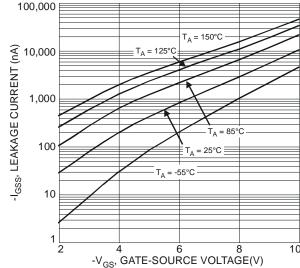
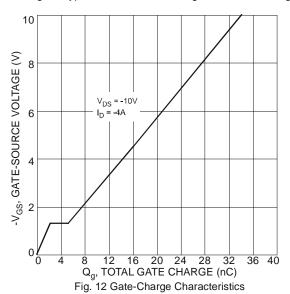
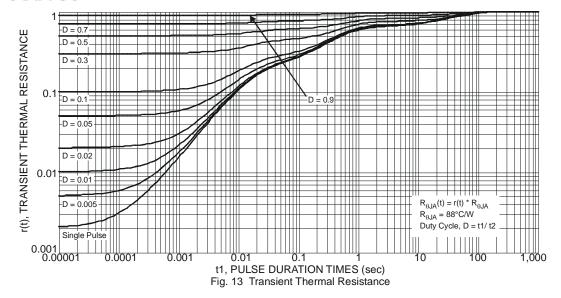


Fig. 10 Typical Gate-Source Leakage Current vs. Voltage

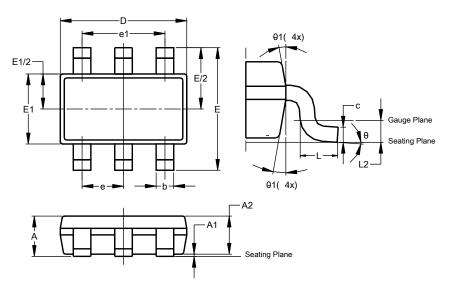






# **Package Outline Dimensions**

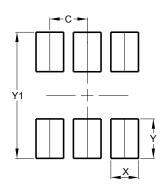
Please see http://www.diodes.com/package-outlines.html for the latest version.



TSOT26						
Dim	Min	Max	Тур			
Α	-	1.00	1			
A1	0.010	0.100	_			
A2	0.840	0.900	-			
D	2.800	3.000	2.900			
Е	2	2.800 BS	С			
E1	1.500	1.700	1.600			
b	0.300 0.450		-			
С	0.120	0.200	_			
е	0.950 BSC					
e1	1	.900 BS	С			
ш	0.30	0.30 0.50 -				
L2	0.250 BSC					
θ	0° 8° 4°		4°			
θ1	4°	12°	-			
All Dimensions in mm						

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.950
Х	0.700
Y	1.000
Y1	3.199



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